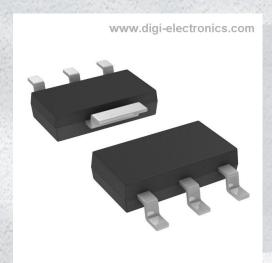


BCP53-10T1G Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number BCP53-10T1G-DG

Manufacturer onsemi

Manufacturer Product Number BCP53-10T1G

Description TRANS PNP 80V 1.5A SOT223

Detailed Description Bipolar (BJT) Transistor PNP 80 V 1.5 A 50MHz 1.5 W

Surface Mount SOT-223 (TO-261)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BCP53-10T1G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	1.5 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
80 V	500mV @ 50mA, 500mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	63 @ 150mA, 2V
Power - Max:	Frequency - Transition:
1.5 W	50MHz
Operating Temperature:	Mounting Type:
-65°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-261-4, TO-261AA	SOT-223 (TO-261)
Base Product Number:	
DCD52	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0075	



PNP Silicon Epitaxial Transistors

BCP53 Series

This PNP Silicon Epitaxial transistor is designed for use in audio amplifier applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

- High Current
- NPN Complement is BCP56
- The SOT-223 Package can be soldered using wave or reflow.
 The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Device Marking:

BCP53T1G = AH

BCP53-10T1G = AH-10

BCP53-16T1G = AH-16

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Surface Mounted)	$R_{\theta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625" from case Time in Solder Bath	TL	260 10	°C s

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

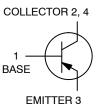
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-80	V
Collector-Base Voltage	V _{CBO}	-100	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	Ic	1.5	Α
	I _{CM}	3.0	Α
Base Current - Continuous	I _B	-0.3	Α
Base Collector Current – Peak, single pulse, $t_p \le 1 \text{ ms}$	I _{BM}	-0.4	Α
Total Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.

1

MEDIUM POWER HIGH CURRENT SURFACE MOUNT PNP TRANSISTORS



MARKING DIAGRAM



SOT-223 CASE 318E STYLE 1



A = Assembly Location

Y = Year W = Work Week

XXXXX = Specific Device Code = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BCP53T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel
NSVBCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BCP53 Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	,		•	•	•
Collector–Base Breakdown Voltage ($I_C = -100 \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	-100	-	-	Vdc
Collector-Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _{(BR)CEO}	-80	-	-	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -100 \mu Adc$, $R_{BE} = 1.0 k\Omega$)	V _{(BR)CER}	-100	-	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	-5.0	-	-	Vdc
Collector-Base Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	_	-	-100	nAdc
Emitter–Base Cutoff Current $(V_{EB} = -5.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	-	-	-100	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_C = -5.0 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ \text{All Part Types} \\ (I_C = -150 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ \text{BCP53, SBCP53} \\ \text{BCP53-10, SBCP53-10} \\ \text{BCP53-16, SBCP53-16, NSVBCP53-16} \\ (I_C = -500 \text{ mAdc, V}_{CE} = -2.0 \text{ Vdc)} \\ \text{All Part Types} \end{array} $	h _{FE}	25 40 63 100 25	- - - -	- 250 160 250 -	-
Collector–Emitter Saturation Voltage ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)	V _{CE(sat)}	-	_	-0.5	Vdc
Base-Emitter On Voltage (I _C = -500 mAdc, V _{CE} = -2.0 Vdc)	V _{BE(on)}	-	-	-1.0	Vdc
DYNAMIC CHARACTERISTICS	,		•	•	•
Current-Gain - Bandwidth Product (I _C = -10 mAdc, V _{CE} = -5.0 Vdc, f = 35 MHz)	f⊤	-	50	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BCP53 Series

TYPICAL CHARACTERISTICS

200

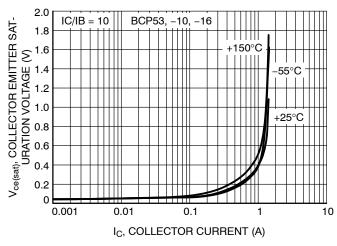
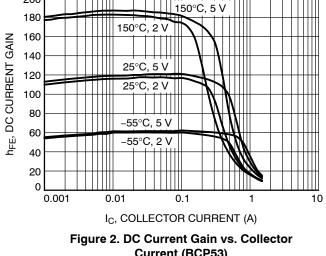


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current



Current (BCP53)

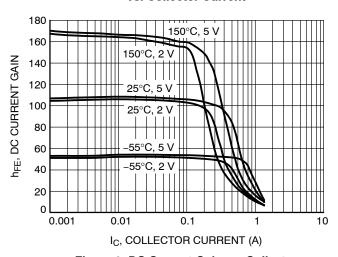


Figure 3. DC Current Gain vs. Collector Current (BCP53-10)

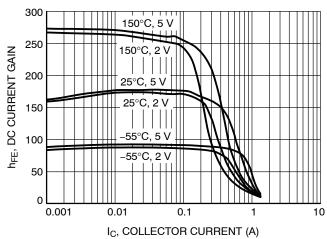


Figure 4. DC Current Gain vs. Collector Current (BCP53-16)

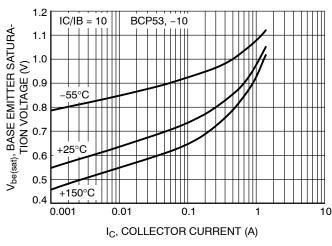


Figure 5. BCP53, -10 Base Emitter Saturation Voltage vs. Collector Current

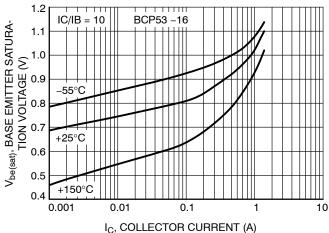
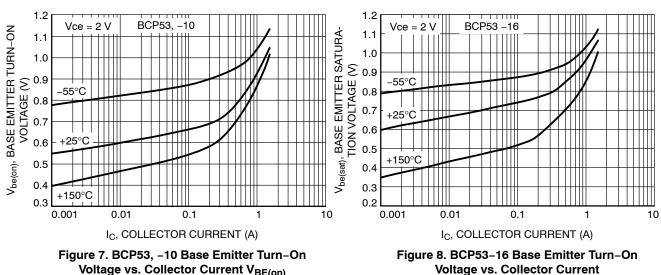


Figure 6. BCP53-16 Base Emitter Saturation Voltage vs. Collector Current

BCP53 Series

TYPICAL CHARACTERISTICS



Voltage vs. Collector Current V_{BE(on)}

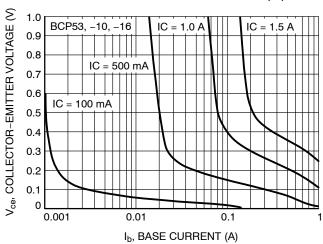


Figure 9. BCP53, -10, -16 Saturation Region

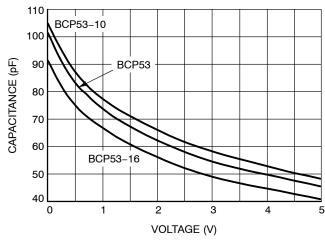


Figure 10. Input Capacitance

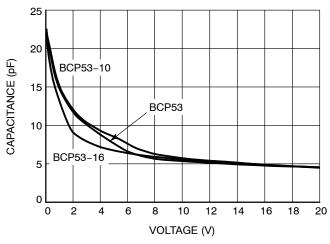


Figure 11. Output Capacitance

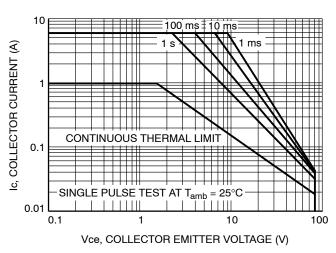


Figure 12. Standard Operating Area

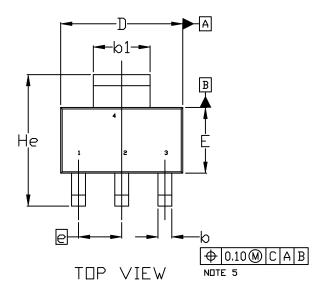


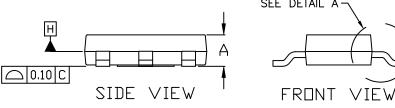
MECHANICAL CASE OUTLINE

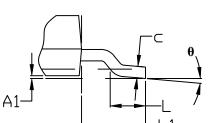
PACKAGE DIMENSIONS



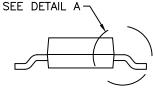
DATE 02 OCT 2018







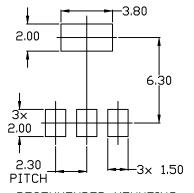
DETAIL A





- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
b	0.60	0.75	0.89	
b1	2.90	2.90 3.06		
c	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
е	2.30 BSC			
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0°		10*	



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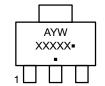
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SOT-223 (TO-261) CASE 318E-04 ISSUE R

DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*



A = Assembly Location

Y = Year W = Work Week

XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)
*This information is generic. Please refer to
device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may
or may not be present. Some products may
not follow the Generic Marking.

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